D ynam ical C orrelation T heory for an E scape P rocess

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Abstract

A dynam ical theory which incorporates the electron-electron correlations and the e ects of external magnetic elds for an electron escaping from a helium surface is presented. The degrees of freedom in the calculation of the escape rate is reduced from 3N to 3 as compared with other approach. Explicit expressions for the escape rate in various situations are obtained. In particular, in the weak parallel magnetic eld lim it the tunneling rate has an exponential dependence quadratic with magnetic eld strength and an unusual exponential increase linear with tem perature.

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W hen many electrons sit in a metastable well near a helium surface, the escape of an electron from the well is no longer a single particle problem due to the C oulom b interaction. E lectron-electron (e-e) correlations play an essential role in the escape process and the physics becomes very rich. This system is ideal to test our understandings of the escape from a metastable well when many body e ects are important. A number of experiments have been performed on the escaping of electrons from a helium surface.?? Recent theoretical studies have mainly concentrated on how the static e-e correlations a ect the escape rate. A comprehensive understanding has been obtained in treating the e-e correlations as either instantaneous following the motion of an escaping electron or not following it at all.?? The real dynam ical nature of the e-e correlations, however, has not been explored adequately. As one can see from a rather similar problem of the escaping of a particle from a metastable well in the presence of an environment, the dynamical response can be dominant.?? In the present paper we develop a dynam ical theory for the escaping of an electron from a helium surface to account for the e ects of both static and dynam ical e-e correlations and m agnetic elds. The original 3N degree freedom problem ?? is simplied to a 3 degree freedom one, with N the total number of electrons in the problem . Expressions in various limits for the escape rate in the term s of tem perature, 2-d electron density, and external magnetic elds are obtained. Particularly, an unusual exponential increase linear with tem perature of the tunneling rate in the presence of a weak parallel magnetic eld is found. The dependence on the magnetic eld is quadratic in exponent in this lim it.

We consider the experimental relevant situation in which the lifetime of the metastable state of an electron is much longer than the relaxation time of the 2-d electrons and the density of 2-d electrons is low such that the Ferm i temperature is the smallest energy in the problem. The escaping events are then statistically independent of each other and the exchange e ect of an escaping electron with 2-d electrons can be ignored. A separation

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between the escaping electron and the remaining 2-d electrons for each escape event can be made. For simplicity, we shall ignore the weaker interactions of the escaping electron to the surface waves of liquid helium and the helium vapor atoms, which has been discussed elsewhere??.

W e start with the derivation of the e ective H am iltonian for the escaping electron classically. This H am iltonian will be the base to study the escape process. For quantum tunneling, an imaginary time path integral method following Ref. [13] will be used. The classical equation of motion for the escaping electron is:

$$m \frac{d^2}{dt^2} R_t = r V_0 (z_t) + \frac{e dR_t}{c dt} B_{ex} + eE_{in} (R_t); \qquad (1)$$

with $V_0(z) = V_w(z) + V_1(z) + V_n(z)$. Here m is the mass of an electron, e is the negative electron charge, c is speed of light, and V_w is the hardwall potential, $V_w = 1$ for z < 0, $V_w = 0$ for z > 0. This potential m in ics the fact that it costs energy leV for an electron to go into the liquid helium, which is very large in the present problem. The in age potential V_i due to the polarization of helium liquid is $V_i(z) = e^2 = z$, with = (1)=4(+1). The dielectric constant of liquid helium = 1.057. The potential V_n is the total electric potential produced by the external applied electric eld (perpendicular only) and the electric eld produced by the mean density n_0 of the 2-d electrons,

$$V_n(z) = e E_{ex} + 2 e(1 \ 4)n_0]z$$
: (2)

The condition for 2-d electron escaping to z = 1 from the surface is $E_{ex} + 2 e(1 \ 4) n_0 < 0$. The external applied magnetic eld is B_{ex} , and E_{in} is the electric eld produced by the 2-d electron density deviated from n_0 .

The induced electric eld E_{in} is generated by the 2-d density deviation from the mean value n_0 , which in turn is induced by the escaping electron. Consequently, E_{in} can be expressed in terms of the motion of the escaping electron. The procedure is as follows.

Let the 2-d electron uid sit on the surface of the liquid helium, the x y plane. The uid is described by a set of hydrodynam ical equations: the continuity equation and the Euler's equation. In the small density deviation and the nonrelativistic limit, we linearize the hydrodynam ical equations. We solve for the density deviation, which is presented by the motion of the plasm a modes. Then using the Poisson equation we obtain the induced electric eld as??

$$E_{in}(R_{t}) = r \frac{Z}{dk} \frac{n_{0}e^{3}}{m} \frac{1}{!^{2}} \frac{1}{!_{p}^{2}(k)} \frac{Z}{2} \exp f kz_{t^{0}} \exp f i(k \# !t^{0})g$$

$$(1 \ 4)^{2} \exp f kz_{t} g \exp f i(k \# !t)g: \qquad (3)$$

Here the plasm a dispersion relation $!_{P}$ (k) in eq.(3) is

$$!_{P}^{2}(\mathbf{k}) = !_{B}^{2} + \frac{n_{0}e^{2}}{m}2 \mathbf{k}(1 - 4) + \frac{k_{B}T}{m}k^{2};$$
 (4)

and the cyclotron frequency $!_{B} = eB_{?ex} = mc$ with $B_{?ex}$ the component of the external magnetic eld perpendicular to the helium surface. In the calculation the pressure $p = nk_{B}T$ for the 2-d classical electron uid phase has been used.

The induced electric eld is contributed by the response of the environment, the plasma modes of 2-d electrons, to the motion of the escaping electron. Hence we are dealing a problem similar to the one in the discussion of the macroscopic quantum elect??, where the total Hamiltonian has three parts, a dissipative environment consisting of harmonic oscillators, a system of interesting, and the coupling between the system and the environment. U sing this analogy, we indicate the following electron:

$$H = \frac{1}{2m} P - \frac{e}{c} A_{ex}^{2} + V_{A} (z) + \sum_{k < g^{p} \overline{n_{0}}}^{Z} dk \frac{X}{j=1/2} - \frac{1}{2m} p_{j}^{2} (k) + \frac{1}{2} m !_{P}^{2} (k)$$

$$q_{j} (k) - \frac{e}{m n_{0} e^{2} (1 - 4) expf kzgc_{j}}{m !_{P}^{2} (k)} \int_{0}^{2} \frac{1}{5} ; \qquad (5)$$

with

$$V_{A}(z) = V_{0}(z) \quad \frac{1}{2} \int_{0}^{z} \int_{0}^{e^{p} \frac{1}{n_{0}}} dk \ 2 \ k \frac{n_{0} e^{4} (1 - 4)^{2}}{m !_{P}^{2} (k)} \exp f \ 2kzg ; \tag{6}$$

and $c_1 = \cos(k - r)$, $g_{\pi} = \sin(k - r)$, $B_{xx} = r - A_{ex}$. Here g is a numerical factor of order unit to be discussed below. The choice of the elective H am iltonian is chosen in a form as in Ref.[14] in the discussion of the dissipative bath in quantum tunneling. When 2-d electrons follow them of the escaping electron completely, the so called the adiabatic limit, the response of 2-d electrons is described by the adiabatic potential given by eq.(6). The deviation from the adiabatic response is described by the plasm a dynamics, the last term in eq.(5). The second term of eq.(6) corresponding to the correlation potential discussed in Ref.[1]. Hence an alternative justicication of its usage in Refs.[1–5] is obtained here. Several features of the electron and the plasm a is highly nonlinear in the coordinate of the escaping electron. The dam ping of the escaping electron due to plasm a is clearly superohm ic case, when $B_{2ex} \in 0.22$. It is also superohm ic when $B_{2ex} = 0$, a situation similar to the polaron problem. The elective H am iltonian contains a weak temperature dependent through the plasm a frequency, which com es from the equilibrium state of the electron uid. The potential $V_A(z)$ is in uenced by B_{2ex} through the plasm a frequency $!_B$ dependence.

Because the average distance between electrons is $1 = p \overline{n_0}$, there is no plasm a mode of large wavenum bers $k >> p \overline{n_0}$. Furtherm ore, the 2-d electron density deviation is large in this regin e and the linearization approximation leading to eqs.(3,4) is not accurate. Then we need to introduce a cuto plasm a frequency $!_c = q \overline{2 \text{ gn}_0^{3=2} e^2} = m \text{ corresponding to } k g^p \overline{n_0}$ which determ ines the fastest response of the plasm a, as shown in Ref.[16]. This would suggest that we could only determ ine the num erical factor g in eq.(6) to be an order of unit, and the radius of the hole created by the escaping electron pushing 2-d electrons sideward?? to be the order of $1 = p \overline{n_0}$. However, g can be theoretically determ ined accurately in the

following way: Let the escaping electron sit in the center of the hole created by itself in 2-d electrons. Because of the rotational symmetry there is no net force from 2-d electrons acting on the escaping electron. The escaping electron only feels the externally applied force, i.e.,

 $r V_A j_{hole center} = e E_{ex} \hat{z}$. The choice of g must satisfy this condition. Therefore we have $g = 2^{p}$. This completes the derivation of the elective H am iltonian eq.(5).

The elective H am iltonian m ay have a wider application region than the region of validity of the hydrodynam ical approach, so long as elementary excitations, such as the plasm a modes calculated above, dominate the response of the 2-d electrons to the escaping electron. For example, this m ay include the case of the W igner lattice phase. In this case, the plasm a modes will be replaced by the phonon modes. One can expect that the form of the electrons is ham iltonian is the same as eq.(5) in the long wave length limit when $B_{2ex} = 0$, because the density deviation is the same longitudinal one. As the local structure of 2-d electrons is not changed in the K osterlitz-T houless transition, we then expect the same short distance behavior. Then there should be no change of the adiabatic potential therefore no change of the escape rate cross the melting tem perature. This is consistent with a recent experiment.??

We now calculate the escape rate starting from eq.(5) for various situations. In the high tem perature regime, the escape is dominated by the therm all activation. The escape rate is $_{T} = A$ expf $E_{b}=k_{B}Tg$. Here the prefactor A is weakly tem perature dependent and is proportional to the density of 2-d electrons. The barrier height E_{b} is determined by the equation $E_{b} = V_{A} (z_{max})$ E_{0} , where z_{max} is the position of the barrier top. The m etastable (ground) state energy E_{0} is directly calculated from the elective Hamiltonian of eq.(5) as

$$E_{0} = \frac{e^{2}}{2a_{B}^{0}} - \frac{1}{2} \int_{0}^{Z} dk \frac{2 k e^{4} n_{0}}{m !_{P}^{2} (k)} (1 - 4)^{2};$$
(7)

with $a_B^0 = h^2 = m e^2$. Much weaker in uences from the Stark shift and vertical spread of 2-d electrons have been ignored. If we ignore its smalle ect on the ground state energy, there

is no in uence of the parallel magnetic eld B_{kex} on the thermal activation rate. On the contrast, the activation rate will be increased in the presence of a perpendicular magnetic eld B_{2 ex}, because B_{2 ex} a ects the potential V_A (z) in a special way. Speci cally, we nd that the barrier height E_b in the weak eld limit as:

$$E_{b} = \begin{cases} 8 \\ \stackrel{\scriptstyle \ensuremath{\mathbb{R}}}{\underset{\scriptstyle \ensuremath{\mathbb{R}}}}{\underset{\scriptstyle \ensuremath{\mathbb{R}}}}{\underset{\scriptstyle \ensuremath{\mathbb{R}}}}{\underset{\scriptstyle \ensuremath{\mathbb{R}}}}{\underset{\scriptstyle \ensuremath{\mathbb{R}}}}{\underset{\scriptstyle \ensuremath{\mathbb{R}}}}}}}}}}}}}}}}}}}}}}}}} } \\ E_{b} = \atop E_{b} = \atop E_{b} = \atop \ensuremath{\mathbb{R}}}}{\underset{\scriptstyle \ensuremath{\mathbb{R}}}}{\underset{\scriptstyle \ensuremath{\mathbb{R}}}}}{\underset{\scriptstyle \ensuremath{\mathbb{R}}}}{\underset{\scriptstyle \ensuremath{\mathbb{R}}}}{\underset{\scriptstyle \ensuremath{\mathbb{R}}}}{\underset{\scriptstyle \ensuremath{\mathbb{R}}}}{}}}}}}}}}} } \\ E$$

This result may be interpreted as that $B_{?ex}$ electricity reduces the interaction between the 2-d electrons and the escaping electron. For a strong magnetic led we should pointed out that the short magnetic length scale introduced by the strong magnetic led may indicate the invalid of the present hydrodynamics approach.

In the low temperature region quantum tunneling dom inates the escape. The tunneling rate is $_{Q} = !_{a} \exp f S_{c}$ =hg. The prefactor $!_{a}$ is of an order of E_{0} =h. The classical action $S_{c} = S_{eff} \mathbb{R}_{c}()$] is evaluated at the classical trajectory $R_{c}()$ determ ined by the equation $S_{eff} \mathbb{R}()$] = 0 which is a 3 instead of 2N + 1 dimensional partial dimensional evaluation, with the elective action S_{eff} as??

$$S_{eff} \mathbb{R} () = S_0 \mathbb{R} () + \frac{1}{2} d^2 d^0 d^0 dk \frac{n_0 e^4 (1 - 4)^2}{4m !_P (k)} \exp [!_P (k) j^0] g^0$$

$$\sum_{k=1}^{n} \exp [k_2 (0) g^2 + 2 \exp [k_2 (0) g^2 + 2 \exp [k_2 (0) g^2] + 2 \exp [k_2 (0) g^2] dk (2 - 2 \exp [k_2 (0) g^2] + 2 \exp [k_2 (0) g^2] dk (2 - 2 \exp [k_2 (0) g^2] dk (2 -$$

with

$$S_0[R()] = \frac{1}{2}mR^2() + \frac{e}{iA_{ex}}R + V_A(z()) :$$
 (10)

The nonlocal term in time in eq.(9) is a result of the reduction of the degrees of freedom from 3N to 3. Numerical calculation can be used in order to make a detailed comparison to experiments. In the following we discuss some prominent features of the tunneling rate analytically. First, we consider the case of the zero parallel magnetic eld $B_{kex} = 0$. If we drop the last and non-negative term in eq.(9), replace R^{-2} by \underline{z}^2 in eq.(10), and apply the 1-d W KB approximation, we obtain a lower bound of the classical action S_c :

$$S_{lower} = 2 \int_{z_1}^{z_2} dz \frac{q}{2m [V_A (z) - E_0]}; \qquad (11)$$

with z_1 and z_2 the turning points which are the solutions of the equation $V_A(z) = 0$. The tunneling rate calculated in this way gives the upper bound for the tunneling rate as pointed out in Refs.[10,11] This upper bound of tunneling rate corresponds to the physical situation in which the 2-d electrons follow the motion of the escaping electron instantaneously, the adiabatic limit, as a general theorem has shown.?? The classical trajectory corresponding the case in which r() = constant therefore $1 cos[k (r() r(^0)] = 0$ (note $B_{kex} = 0$). Setting expf $kz(^0)g = 1$, integrating over 0 , and again using the 1-d W KB approximation, we obtain an upper bound for S_c from eq.(9):

$$S_{upper} = 2 \frac{\sum_{z_1^0}^{Z} dz}{\sum_{z_1^0}^{Q} dz} \frac{q}{2m [V_U (z) - E_0]};$$
(12)

with z_1^0 and z_2^0 the turning points which are the solution of the equation $V_U(z) = 0$. Here the potential $V_U(z)$ is

$$V_{\rm U}(z) = V_{\rm A}(z) + \frac{1}{4} \frac{\sum_{0}^{2} g^{\rm p} \overline{n_{\rm o}}}{0} dk \frac{2 \ ke^{4} n_{0}(1)^{2}}{m !_{\rm P}^{2}(k)} (\exp f \ kzg \ 1)^{2} ; \qquad (13)$$

This upper bound for S_c is smaller than that given by the frozen potential??, and is a better one. This is due to the partial inclusion of the dynam ics of the plasm a modes.

The tunneling rate increases as B_{2ex}^2 in the low eld limit because of the suppression of the correlation potential discussed in the case of therm all activation rate. There is another reason for the increase of tunneling rate, the increase of the adiabaticity: If we x the adiabatic potential V_A (z), and allow the plasm a frequencies to increase independently, then the e-e response will be able to follow the motion of escaping electron more closely, and

 S_c decreases towards its lower bound, S_c ! S_{lower} , the adiabatic limit. This result is the opposite of R ef.[10]. Because the damping is superohmic, the temperature dependence due to damping in the tunneling regime is found to behave as 0 (T⁷) and is small in the low temperature limit.??

Now we discuss the case that the parallelm agnetic eld is present, $B_{kex} \in 0$ and $B_{?ex} = 0$. By choosing the parallel magnetic eld along the x-direction and $A_{ex} = (0; B_{kex}z; 0)$, according to the elective H am iltonian eq.(5) we have the rst two terms as

$$H_{0} = \frac{1}{2m} P_{z}^{2} + V_{A} (z) + \frac{1}{2m} P_{y} + \frac{e}{c} B_{kex} z^{2} :$$
(14)

The x-direction motion is irrelevant. This H am iltonian describes the 1-d motion of a particle coupling to a harmonic oscillator with a zero frequency. We integrate over the y coordinate to obtain the elective action for the motion in z direction as

$$S_{eff}[z()] = \begin{bmatrix} z \\ d \end{bmatrix} = \begin{bmatrix} z \\ 2 \end{bmatrix} + V_{A}(z()) + \frac{1}{4m} = \frac{eB_{kex}}{c} \begin{bmatrix} z \\ h \end{bmatrix}^{2} \begin{bmatrix} z \\ b \end{bmatrix}^{2} = \begin{bmatrix} z \\ d \end{bmatrix}^{2} \begin{bmatrix} z \\ 0 \end{bmatrix} \begin{bmatrix} z \\ 0 \end{bmatrix}^{2} = \begin{bmatrix} z \\ 0$$

This result suggests that the y direction motion acting as a dissipative environment to the z direction motion.?? The in uence action from the plasma modes is ignored by assuming the adiabatic limit for simplicity, which will be discussed below. In the small eld limit, the classical trajectory remains unchanged. The classical action can then be evaluated perturbatively:

$$S_{c} = S_{low er} + \frac{1}{2m} - \frac{eB_{kex}}{c} d_{z_{c}^{2}} d_{z_{c}^$$

with sem iclassical trajectory z_c () determined by the usual equation $\frac{1}{2}m \ \underline{z}_e^2 = V_A (z_c) \quad E_0$. The tunneling rate decreases at zero temperature because of the bending of classical trajectory, and increases exponentially with temperature because of the excitation of the y-direction motion, with a B_{kex}^2 dependence on the parallel magnetic eld. In the calculation we have ignored a weak dependence of E_0 on B_{kex} .

We have discussed the crossing from them all activation to quantum tunneling, the e ect of the correlation potential, the dynamical response of the 2-d electrons to the escaping electron, and the e ect of weak parallel magnetic eld. We now discuss the conditions to observe these e ects. Let $!_{b}^{2} = j Y_{a}^{0} (z_{max}) j = b$ the small oscillation frequency in the inverse potential $V_{A}(z)$. The crossing from them all activation to quantum tunneling occurs at $k_{B}T_{0} = h!_{b}$ according to the standard theory.??. The frequency $!_{b}$ also determ ines the dynamics of the escaping electron in the inverse potential. In order for the 2-d electrons to follow the motion of the escaping electron, the cuto plasm a frequency should satis es the inequality $!_{c} > !_{b}$, and then the tunneling is essentially an adiabatic process??. Sim ilarly, the condition for the weak parallel magnetic eld B_{kex} is $eB_{kex} = m c < !_{b}$. To manifest the correlation e ect in the escape process, we need $P \overline{n_{0}} z_{max} = 1$ in the case of the thermal activation, and $P \overline{n_{0}} z_{2} = 1$ in the case of quantum tunneling, otherwise the correlation e ect is small.

Finally, let us make a brief comparison to experiments. The present theory is in agreement with experiments in the thermal activation regime, where consistent experimental data exist.?? The existing quantum tunneling data in the absence of magnetic eld?? do not agree with each other and there is no satisfactory explanation. However, the magnetic eld dependent tunneling results obtained in the present paper, the quadratic dependence on the parallel magnetic eld and linear in temperature, agree with a recent experiment described in Ref.[5].

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